NSN 5962-01-446-9761

Memory Microcircuit - Page 1 of 1



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| Maximum Power Dissipation Rating: |
|--|
| 1.0 watts |
| Operating Tempurature Range: |
| -55.0/+125.0 degrees celsius |
| Storage Tempurature Range: |
| -65.0/+150.0 degrees celsius |
| Features Provided: |
| Monolithic and electrostatic sensitive and low power and burn in, mil-std-883, class b |
| Inclosure Material: |
| Ceramic and glass |
| Inclosure Configuration: |
| Dual-in-line |
| Output Logic Form: |
| Complementary-metal oxide-semiconductor logic |
| Terminal Surface Treatment: |
| Solder |
| Product Name: |
| Microcircuit, memory, digital, cmos, 128k x 8 static random access memory (sram) low power |
| Voltage Rating And Type Per Characteristic: |
| -0.5 volts input and 7.0 volts input |
| Time Rating Per Chacteristic: |
| 85.00 nanoseconds access |
| Memory Device Type: |
| Ram |
| Special Features: |
| Circuit function-dual ce |
| Test Data Document: |
| 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). |
| Terminal Type And Quantity: |
| 32 printed circuit |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| No |
| Fiig: |
| A458a0 |
| |